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Declarations under Rule 4.17:

- as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))
- as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))

[Continued on next page]

(54) Title: CMP COMPOSITIONS AND METHODS FOR SUPPRESSING POLYSILICON REMOVAL RATES

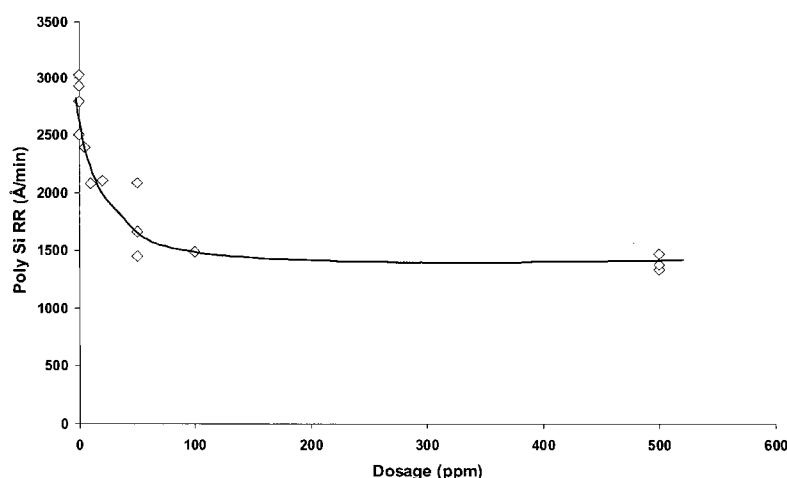


FIG. 2

(57) Abstract: The present invention provides a chemical-mechanical polishing (CMP) composition suitable for polishing a silicon nitride-containing substrate while suppressing polysilicon removal from the substrate. The composition comprises abrasive particles suspended in an acidic aqueous carrier containing a surfactant comprising an alkyne-diol, an alkyne diol ethoxylate, or a combination thereof. Methods of polishing a semiconductor substrate therewith are also disclosed.

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